

BAS40W SERIES SCHOTTKY DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^\circ\text{C}$)

Collector current

I_F : 200 mA

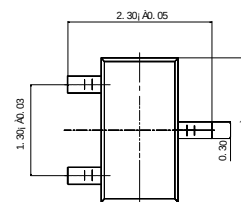
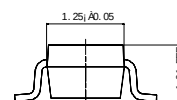
Collector-base voltage

V_R : 40 V

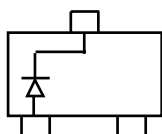
Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150^\circ\text{C}$

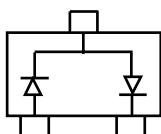
SOT-323



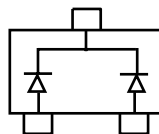
Unit: mm



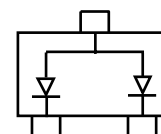
BAS40W Marking: 43.K43



BAS40W-04 Marking: 44.K44



BAS40W-05 Marking: 45.K45



BAS40W-06 Marking: 46.K46

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R = 10\mu\text{A}$	40		V
Reverse voltage leakage current	I_R	$V_R = 30\text{V}$		200	nA
Forward voltage	V_F	$I_F = 1\text{mA}$ $I_F = 40\text{mA}$		380 1000	mV
Diode capacitance	C_D	$V_R = 0\text{V}, f = 1\text{MHz}$		5	pF
Reveres recovery time	t_{rr}	$I_F = 10\text{mA}$ through $I_R = 10\text{mA}$ to $I_R = 1\text{mA}$		5	nS